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Docket Number (Optional)	Application Number
FIS920030102 .1	
Applicant(s)	
Chen et al.	
Filing Date	**Group Art Unit**

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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

		H. Akatsu et al., "A highly manufacturable 110nm DRAM technology with 8F2 vertical transistor cell for 1Gb and beyond", IEEE 2002 Symposium on VLSI Technology Digest of Technical Papers K. McStay et al., "Vertical pass transistor design for sub-100nm DRAM technologies", IEEE 2002 Symposium on VLSI Technology Digest of Technical Papers
		J. A. Mandelman et al., "Challenges and future directions for the scaling of dynamic random-access memory (DRAM)", IBM Journal of Research and Development, Vol. 46, No. 2/3, March/May 2002, pp. 187 - 208

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Docket Number (Optional)	Application Number
FIS920030102US1	10/622,477
Applicant(s)	
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Filing Date	**Group Art Unit**
7/18/2003	2818

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